

**Höchstzulässige Werte / Maximum rated values****Elektrische Eigenschaften / Electrical properties**

Kollektor-Emitter-Sperrspannung collector-emitter voltage		V_{CES}	1200	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ\text{C}$	$I_{C,nom.}$	150	A
	$T_C = 25^\circ\text{C}$	I_C	200	A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 80^\circ\text{C}$	I_{CRM}	300	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ\text{C}$, Transistor	P_{tot}	1050	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V
Dauergleichstrom DC forward current		I_F	150	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	I_{FRM}	300	A
Grenzlastintegral der Diode I^2t - value, Diode	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^\circ\text{C}$	I^2t	12	kA^2s
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	V_{ISOL}	2,5	kV

Charakteristische Werte / Characteristic values**Transistor / Transistor**

min. typ. max.

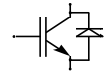
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 150\text{A}, V_{GE} = 15\text{V}, T_{vj} = 25^\circ\text{C}$	$V_{CE\text{ sat}}$	-	2,5	3	V
	$I_C = 150\text{A}, V_{GE} = 15\text{V}, T_{vj} = 125^\circ\text{C}$		-	3,1	3,7	V
Gate-Schwellenspannung gate threshold voltage	$I_C = 6\text{mA}, V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}$	$V_{GE(th)}$	4,5	5,5	6,5	V
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 25\text{V}, V_{GE} = 0\text{V}$	C_{ies}	-	10	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}$	I_{CES}	-	0,01	1	mA
	$V_{CE} = 1200\text{V}, V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}$		-	8		mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^\circ\text{C}$	I_{GES}	-	-	320	nA

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date of publication: 2003-12-09

approved by: Robert Severin

revision: 3.1



Charakteristische Werte / Characteristic values

Transistor / Transistor

min. typ. max.

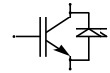
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = 150A, V_{CE} = 600V$	$t_{d,on}$	-	0,07	-	μs
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 125^\circ C$					
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 150A, V_{CE} = 600V$	t_r	-	0,05	-	μs
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 125^\circ C$					
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = 150A, V_{CE} = 600V$	$t_{d,off}$	-	0,45	-	μs
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 125^\circ C$					
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 150A, V_{CE} = 600V$	t_f	-	0,034	-	μs
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 25^\circ C$					
	$V_{GE} = \pm 15V, R_G = 5,6\Omega, T_{vj} = 125^\circ C$					
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 150A, V_{CE} = 600V, V_{GE} = 15V$	E_{on}	-	24,4	-	mWs
	$R_G = 5,6\Omega, T_{vj} = 125^\circ C, L_S = 80nH$					
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 150A, V_{CE} = 600V, V_{GE} = 15V$	E_{off}	-	12,7	-	mWs
	$R_G = 5,6\Omega, T_{vj} = 125^\circ C, L_S = 80nH$					
Kurzschlußverhalten SC Data	$t_p \leq 10\mu sec, V_{GE} \leq 15V, R_G = 5,6\Omega$	I_{SC}	-	1200	-	A
	$T_{vj} \leq 125^\circ C, V_{CC} = 720V, V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$					
Modulinduktivität stray inductance module		L_{SCE}	-	35	-	nH

Charakteristische Werte / Characteristic values

Diode / Diode

min. typ. max.

Durchlaßspannung forward voltage	$I_F = 150A, V_{GE} = 0V, T_{vj} = 25^\circ C$	V_F	-	2,3	2,8	V
	$I_F = 150A, V_{GE} = 0V, T_{vj} = 125^\circ C$					
Rückstromspitze peak reverse recovery current	$I_F = 150A, -di_F/dt = 2500A/\mu sec$	I_{RM}	-	160	-	A
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 25^\circ C$					
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 125^\circ C$					
Sperrverzögerungsladung recovered charge	$I_F = 150A, -di_F/dt = 2500A/\mu sec$	Q_r	-	13	-	μAs
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 25^\circ C$					
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 125^\circ C$					
Abschaltenergie pro Puls reverse recovery energy	$I_F = 150A, -di_F/dt = 2500A/\mu sec$	E_{rec}	-	3,1	-	mWs
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 25^\circ C$					
	$V_R = 600V, V_{GE} = -15V, T_{vj} = 125^\circ C$					

**Thermische Eigenschaften / Thermal properties**

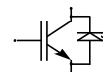
			min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Transistor / transistor, DC	R_{thJC}	-	-	0,12	K/W
	Diode/Diode, DC		-	-	0,28	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Zweig / per arm $d_{paste} \leq 50\mu m$ / $d_{grease} \leq 50\mu m$	R_{thCK}	-	-	0,012	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature		T_{op}	-40	-	125	°C
Lagertemperatur storage temperature		T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see appendix				
Innere Isolation internal insulation			AlN	
Kriechstrecke creepage distance			20	mm
Luftstrecke clearance			11	mm
CTI comperative tracking index			225	
Anzugsdrehmoment f. mech. Befestigung mounting torque		M1	3	6 Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	terminals M4	M2		Nm
	terminals M8			Nm
Gewicht weight		G	300	g

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert.
Sie gilt in Verbindung mit den zugehörigen Technischen Erläuterungen.

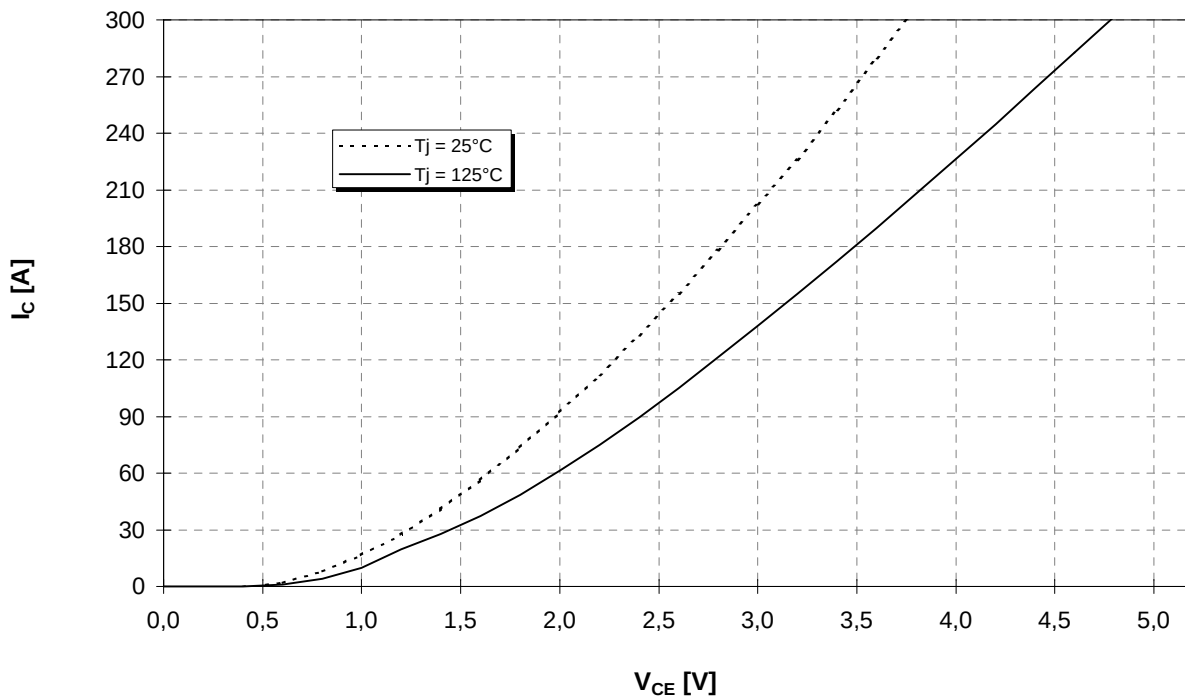
This technical information specifies semiconductor devices but promises no characteristics. It is
valid in combination with the belonging technical notes.



Ausgangskennlinie (typisch)
Output characteristic (typical)

$$I_c = f(V_{CE})$$

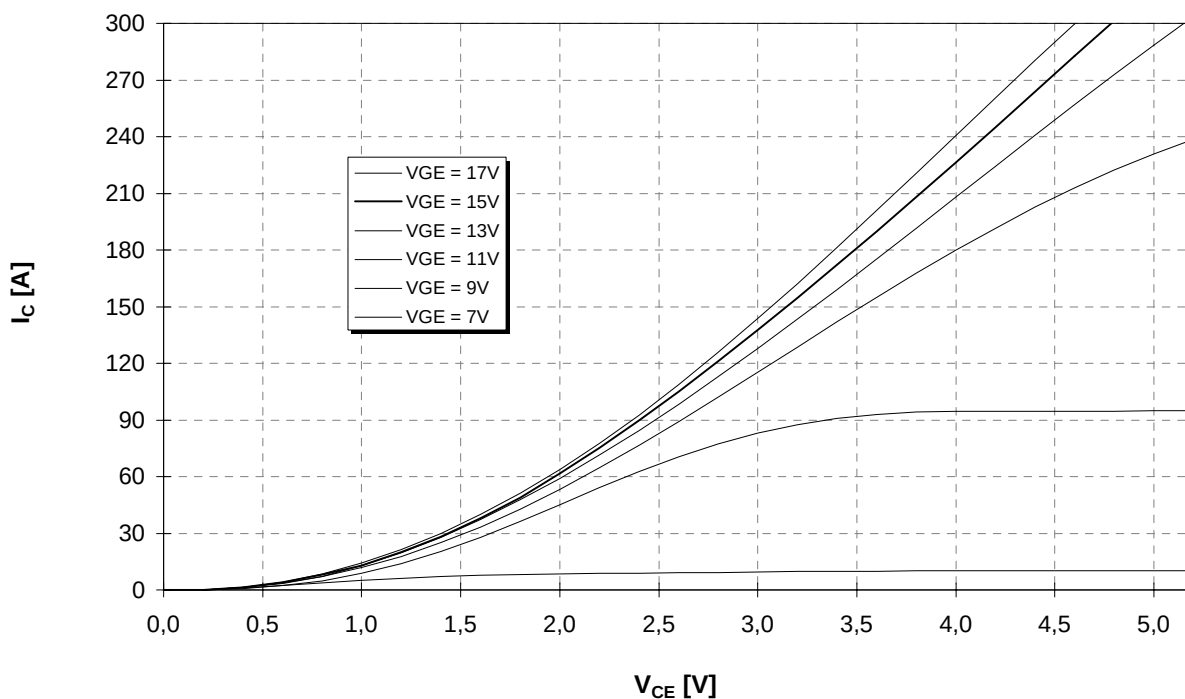
$V_{GE} = 15V$

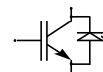


Ausgangskennlinienfeld (typisch)
Output characteristic (typical)

$$I_c = f(V_{CE})$$

$T_{vj} = 125^\circ C$

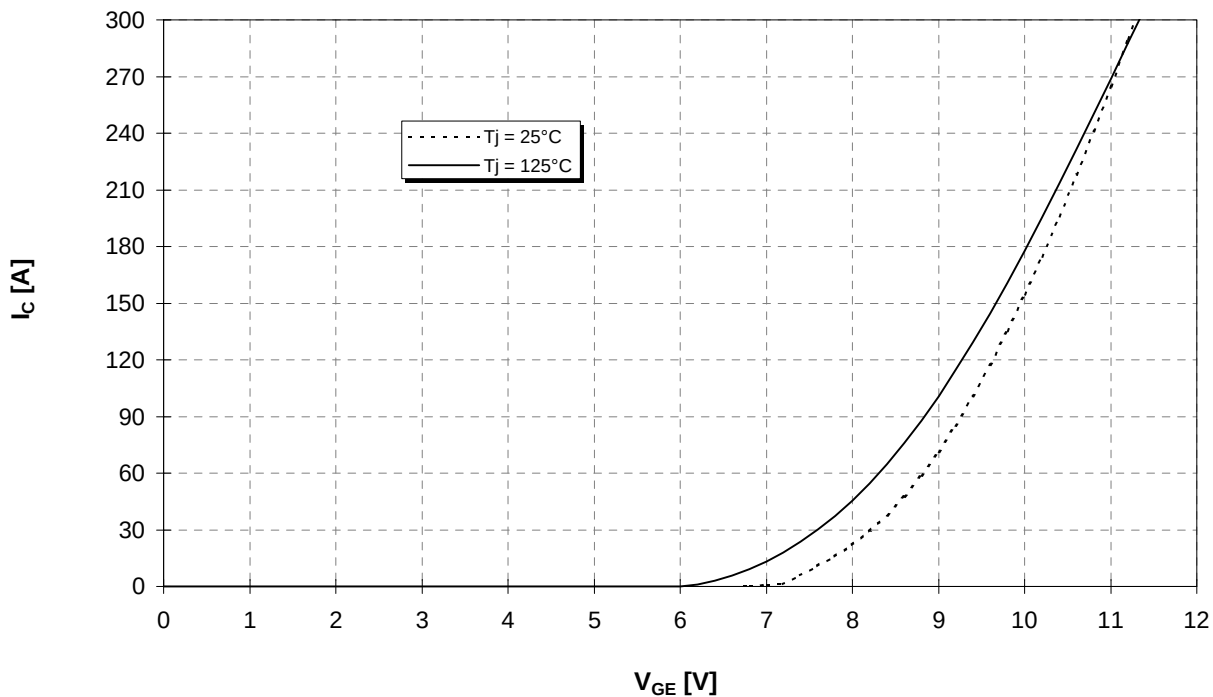




Übertragungscharakteristik (typisch)
Transfer characteristic (typical)

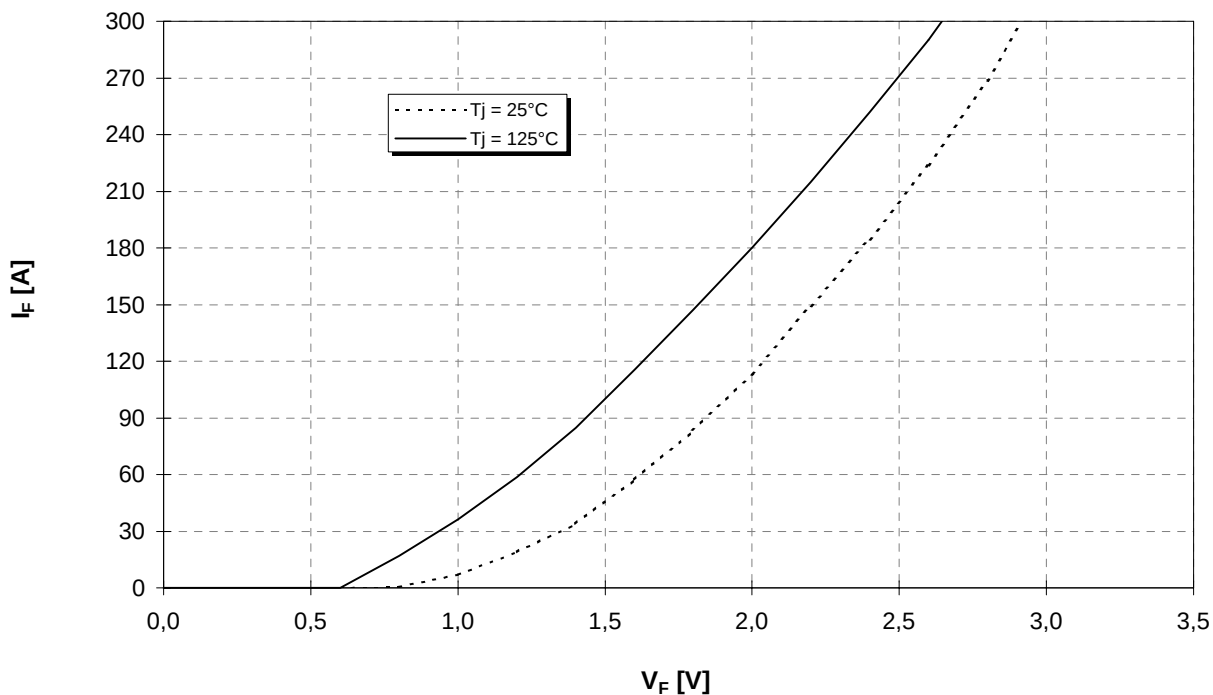
$$I_c = f(V_{GE})$$

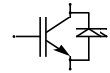
$V_{CE} = 20V$



Durchlaßkennlinie der Inversdiode (typisch)
Forward characteristic of inverse diode (typical)

$$I_F = f(V_F)$$

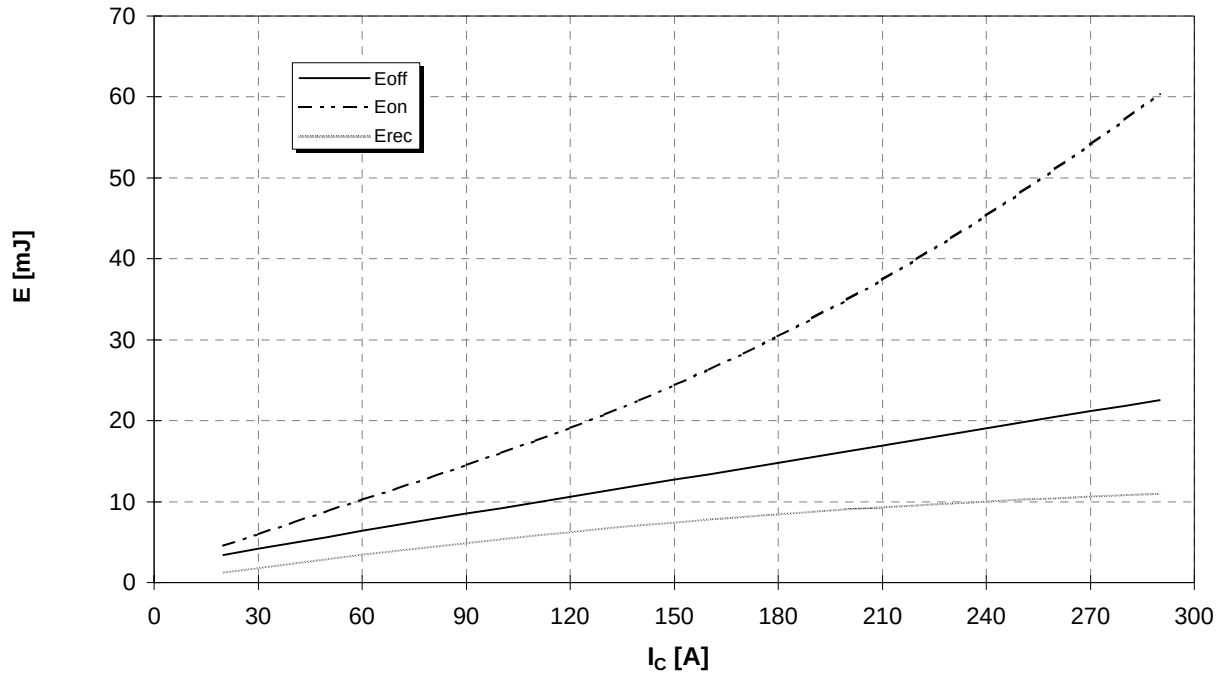




Schaltverluste (typisch)
Switching losses (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$, $E_{rec} = f(I_C)$

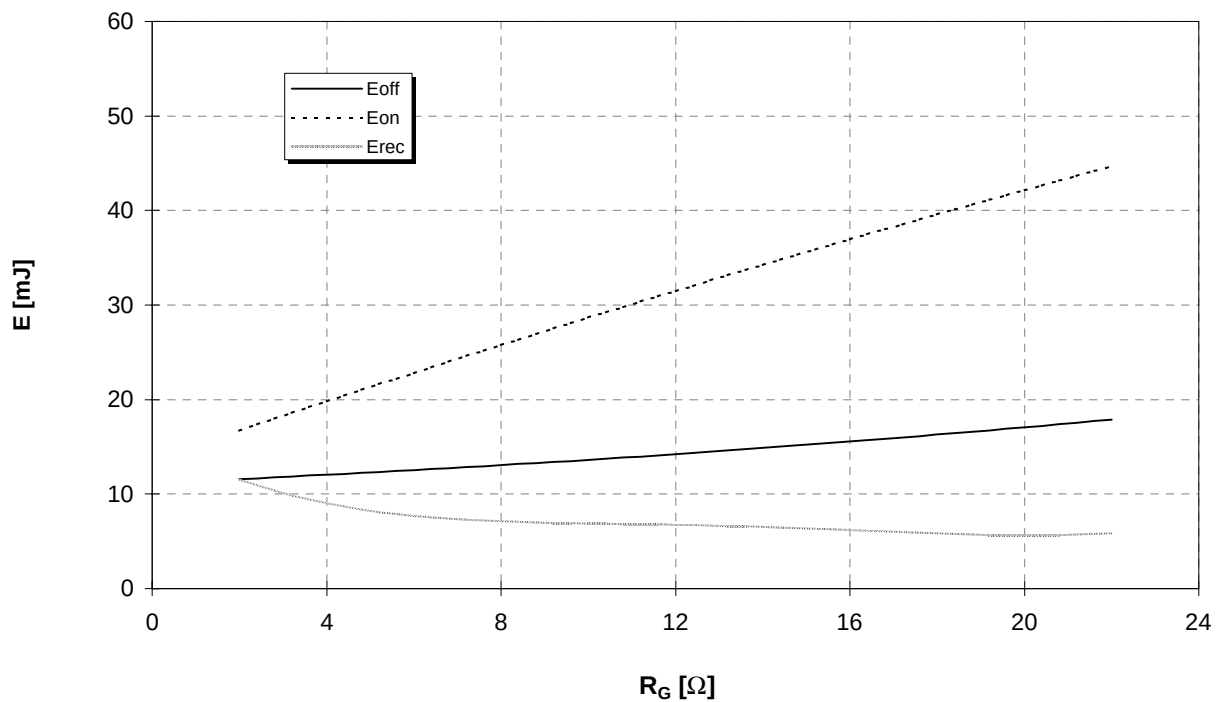
$R_{gon} = R_{goff} = 5,6 \Omega$, $V_{CE} = 600V$, $T_J = 125^\circ C$



Schaltverluste (typisch)
Switching losses (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{rec} = f(R_G)$

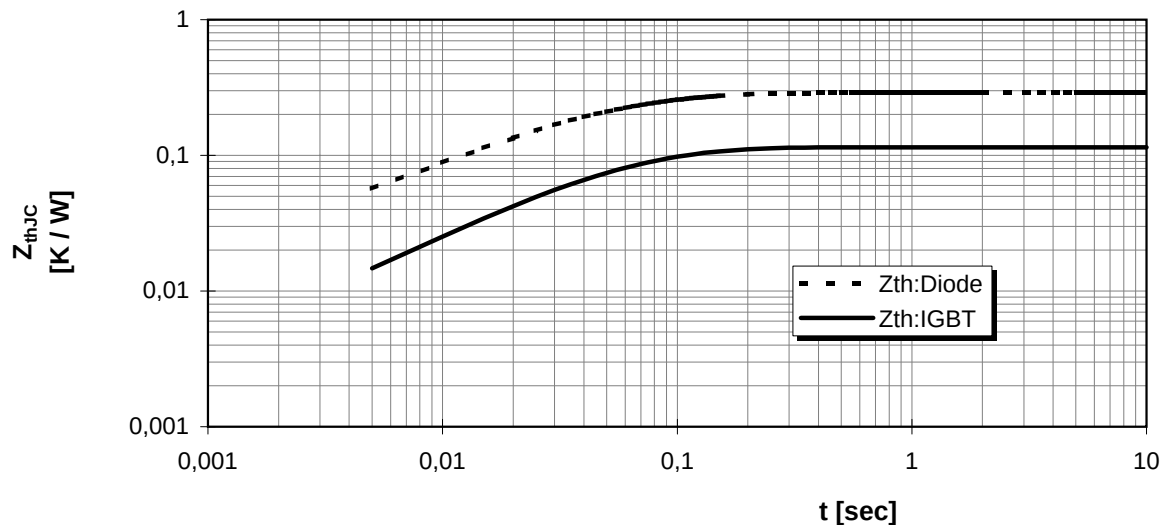
$I_C = 150A$, $V_{CE} = 600V$, $T_J = 125^\circ C$





Transienter Wärmewiderstand Transient thermal impedance

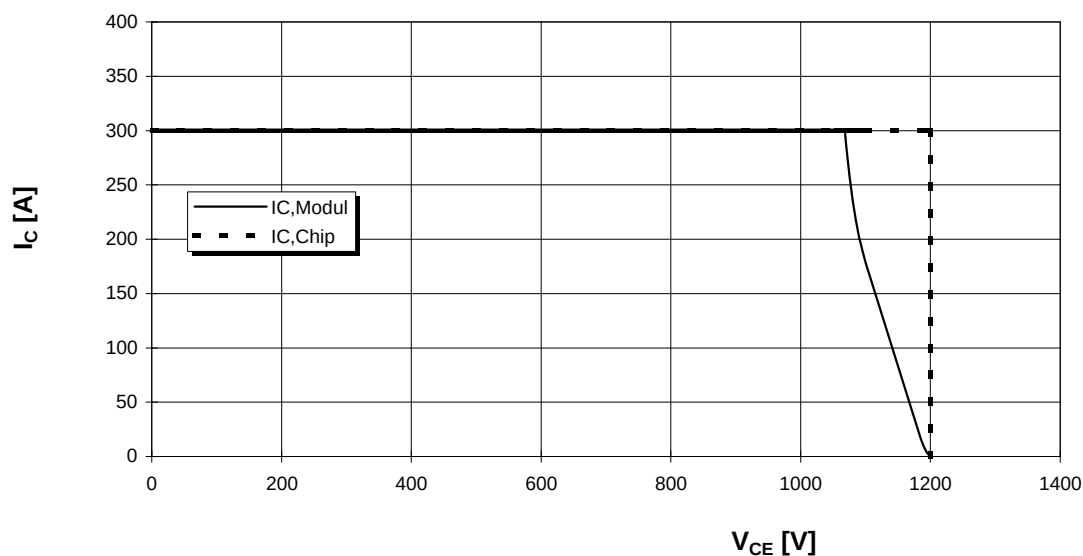
$$Z_{thJC} = f(t)$$

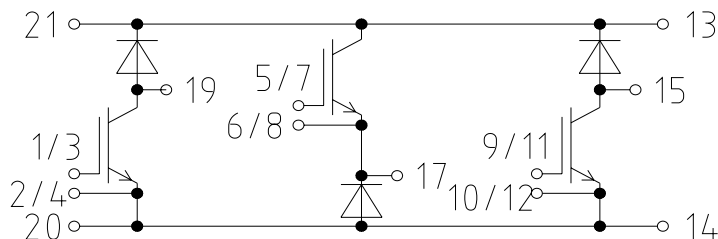
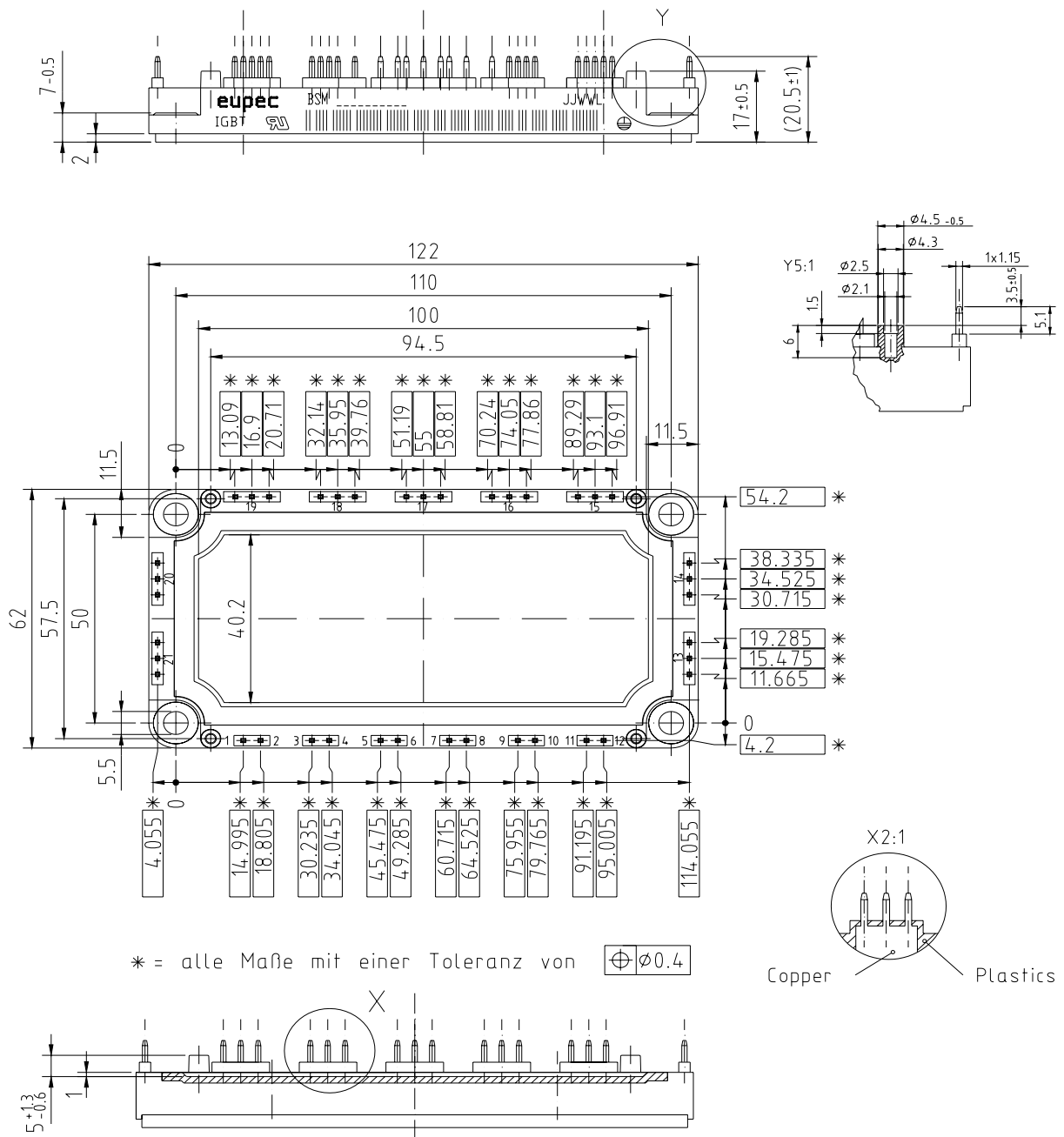


i	1	2	3	4	5	6
r_i [K/kW] : IGBT	0,00001	0,046308	0,053652	0,012162	0,002541	0,005278
τ_i [sec] : IGBT	277,9483	0,075179	0,0411	0,017635	0,002617	0,000562
r_i [K/kW] : Diode	0,00001	0,153993	0,103323	0,00912	0,021627	0
τ_i [sec] : Diode	277,9483	0,06179	0,020533	0,01968	0,001761	0

Sicherer Arbeitsbereich (RBSOA)

Reverse bias safe operation area (RBSOA)

 $R_g = 5,6 \text{ Ohm}, T_{vj} = 125^\circ\text{C}$




Pin 16 and 18 are not connected.

All gate pin's (1,3,5,7,9,11) and all auxiliary emitter pin's (2,4,6,8,10,12) must be connected !

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